

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

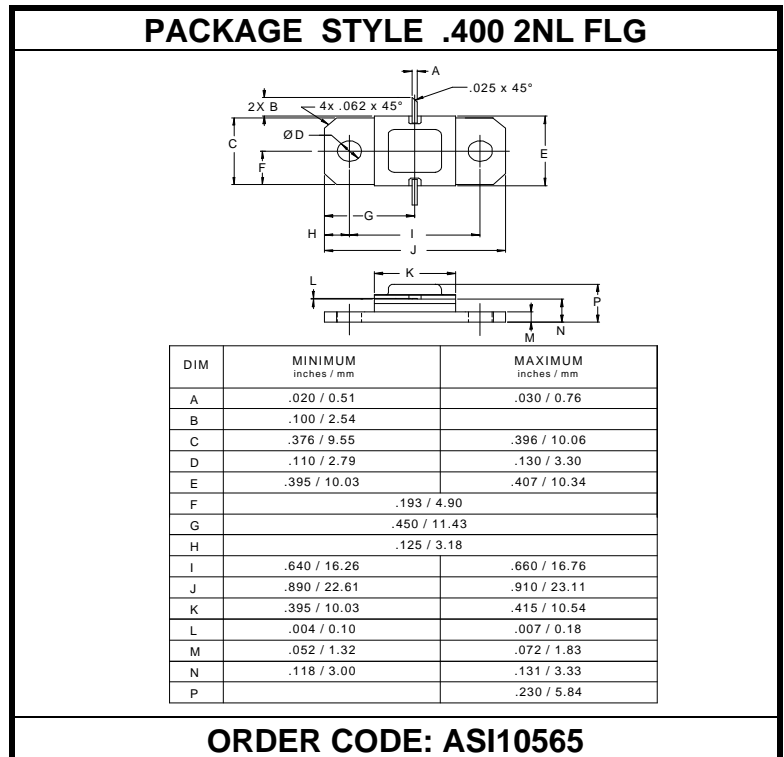
The **ASI AVD250** is Designed for

**FEATURES:**

- Input Matching Network
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	17.8 A
<b>V<sub>CC</sub></b>	55 V
<b>P<sub>DISS</sub></b>	600 W @ T <sub>C</sub> ≤ 80 °C
<b>T<sub>J</sub></b>	-65 °C to +250 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	0.2 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 10 mA	65			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 25 mA      R <sub>BE</sub> = 10 Ω	65			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1 mA	3.5			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 50 V			25	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	15		120	<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 50 V      P <sub>OUT</sub> = 250 W      f = 1025 - 1150	6.2			<b>dB</b>
<b>η<sub>C</sub></b>	MHZ	40			<b>%</b>